



MMDT3904VC

DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

Epitaxial Planar Die Construction

Ideal for Low Power Amplification and Switching

Ultra-Small Surface Mount Package

Lead Free By Design/RoHS Compliant (Note 4) "Green Device" (Note 5)

Mechanical Data

Case: SOT-563

Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020C Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208

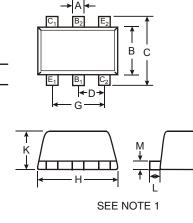
Terminal Connections: See Diagram

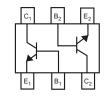
Marking (See Page 2): APK

Ordering Information: See Below

Date Code Information: See Page 2

Weight: 0.003 grams (approximate)





SOT-563											
Dim	Dim Min Max Typ										
Α	0.15	0.30	0.25								
В	1.10	1.25	1.20								
С	1.55 1.70 1.60										
D	0.50										
G	0.90	1.10	1.00								
Н	1.50	1.70	1.60								
К	0.56 0.60 0.60										
L	0.10	0.20									
М	0.10	0.18									
All	All Dimensions in mm										

Maximum Ratings @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	Ι _C	200	mA
Power Dissipation (Note 2)	Pd	200	mW
Thermal Resistance, Junction to Ambient	R JA	625	C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	С

Ordering Information (Note 3)

Device	Packaging	Shipping
MMDT3904VC-7	SOT-563	3000/Tape & Reel

Notes: 1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180 rotated, or mixed (both ways).

 Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

4. No purposefully added lead.

5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

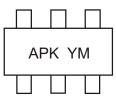


Characteristic	Symbol	Min	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 6)								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60		V	$I_{\rm C} = 10$ A, $I_{\rm E} = 0$			
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40		V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$			
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0		V	$I_{\rm E} = 10$ A, $I_{\rm C} = 0$			
Collector Cutoff Current	I _{CEX}		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$			
Base Cutoff Current	I _{BL}		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$			
ON CHARACTERISTICS (Note 6)								
DC Current Gain	h _{FE}	40 70 100 60 30	300		$ \begin{array}{ll} I_{C} = \ 100\mu A, \ V_{CE} = \ 1.0V \\ I_{C} = \ 1.0mA, \ V_{CE} = \ 1.0V \\ I_{C} = \ 10mA, \ V_{CE} = \ 1.0V \\ I_{C} = \ 50mA, \ V_{CE} = \ 1.0V \\ I_{C} = \ 100mA, \ V_{CE} = \ 1.0V \\ \end{array} $			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.20 0.30	V	$\begin{array}{l} I_C = 10 m A, \ I_B = 1.0 m A \\ I_C = 50 m A, \ I_B = 5.0 m A \end{array}$			
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	$\label{eq:IC} \begin{array}{l} I_C = 10 m A, \ I_B = 1.0 m A \\ I_C = 50 m A, \ I_B = 5.0 m A \end{array}$			
SMALL SIGNAL CHARACTERISTICS								
Output Capacitance	C _{obo}		4.0	pF	$V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$			
Input Capacitance	C _{ibo}		8.0	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$			
Input Impedance	h _{ie}	1.0	10	k				
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,			
Small Signal Current Gain	h _{fe}	100	400		f = 1.0 kHz			
Output Admittance	h _{oe}	1.0	40	S				
Current Gain-Bandwidth Product	f _T	300		MHz	$\label{eq:VCE} \begin{array}{l} V_{CE} = 20V, \ I_C = 10mA, \\ f = 100MHz \end{array}$			
Noise Figure			5.0	dB				
SWITCHING CHARACTERISTICS								
Delay Time	t _d		35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$			
Rise Time	tr		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$			
Storage Time	ts		200	ns	$V_{CC} = 3.0V, I_C = 10mA,$			
Fall Time	t _f		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$			

Electrical Characteristics @ T_A = 25 C unless otherwise specified

Notes: 6. Short duration test pulse used to minimize self-heating.

Marking Information

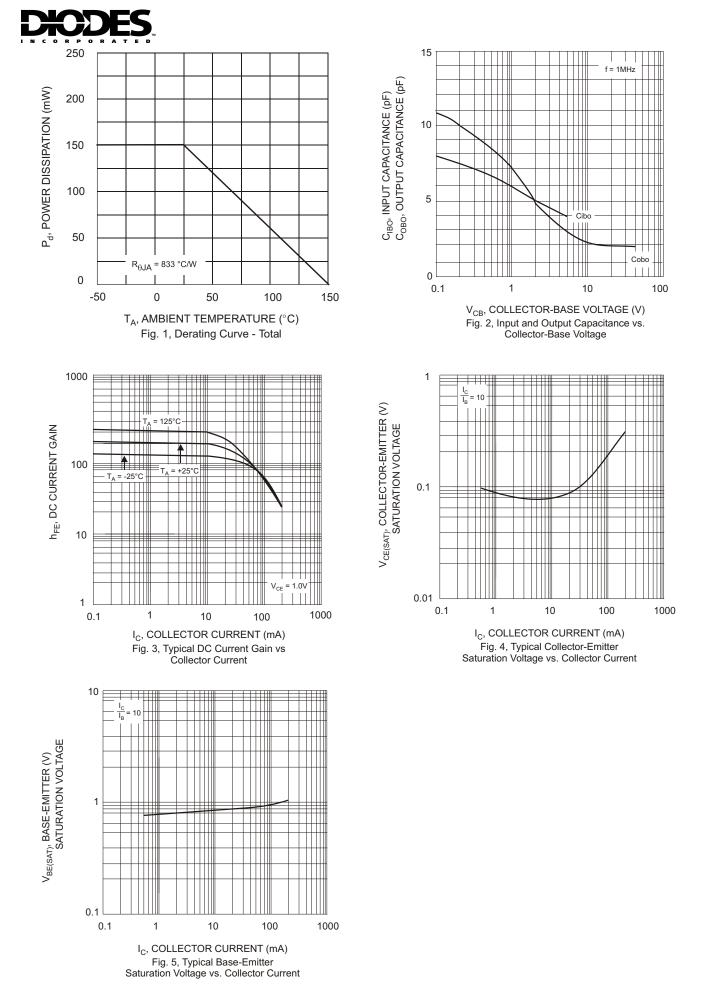


 $\begin{array}{l} \mathsf{APK}=\mathsf{Product}\ \mathsf{Type}\ \mathsf{Marking}\ \mathsf{Code}\\ \mathsf{YM}=\mathsf{Date}\ \mathsf{Code}\ \mathsf{Marking}\\ \mathsf{Y}=\mathsf{Year}\ \mathsf{ex:}\ \mathsf{R}=2004\\ \mathsf{M}=\mathsf{Month}\ \mathsf{ex:}\ 9=\mathsf{September} \end{array}$

Date Code Key

Year	2005	2006	2007	2008	2009	2010	2011	2012
Code	S	Т	U	V	W	Х	Y	Z

[Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D





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